



## 1. Description

JRP02N08, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for BMS and high current switching applications.

### KEY CHARACTERISTICS

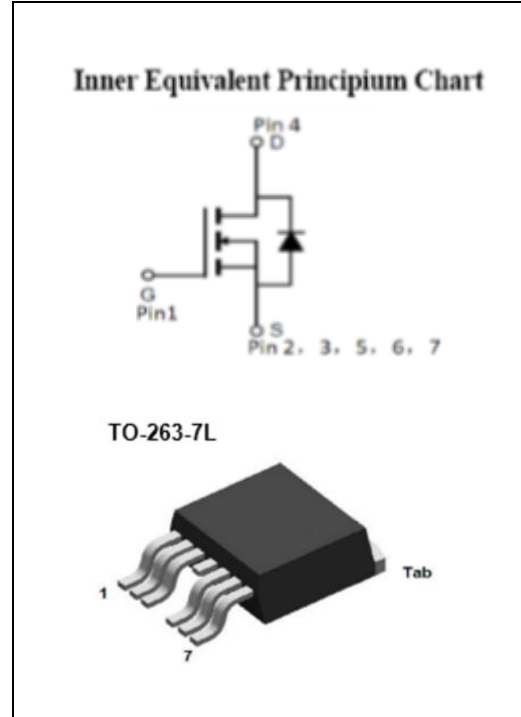
Parameter	Value	Unit
V <sub>DSS</sub>	85	V
I <sub>D</sub>	300	A
R <sub>DS(on).typ</sub>	1.4	mΩ

### FEATURES

- Fast Switching
- Low On-Resistance (  $R_{DS(on)} \leq 2m\Omega$  )
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

### APPLICATIONS

- BMS
- High current switching applications



## ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
JRP02N08-BA	TO263-7	P02N08	Reel

<p><u>JRP02N08-BA</u></p> <div style="border: 1px solid black; padding: 5px; display: inline-block;"> <p>(2) Package type</p> <p>(1) Chip name</p> </div> <p>(1) JRP02N08: 2mΩ/85V (2) BA: TO263-7</p>	<div style="border: 1px solid black; padding: 5px; display: inline-block;"> <p> XXXXX YYWW ZZ SSSSS</p> </div> <p>XXXXX: Product Code YYWW: Year&amp;Week ZZ: Assembly Code SSSSS: Lot Code</p>
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## 2. ABSOLUTE RATINGS

at  $T_C=25^{\circ}\text{C}$ , unless otherwise specified

Symbol	Parameter	Rating	Units
$V_{DSS}$	Drain-Source Voltage	85	V
$I_D$	Continuous Drain Current, Silicon Limited	349	A
	Continuous Drain Current, Package Limited	300	A
	Continuous Drain Current @ $T_C=100^{\circ}\text{C}$ , Silicon Limited	220.7	A
$I_{DM}$ <sup>Note1</sup>	Pulsed Drain Current	1200	A
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$E_{AS}$ <sup>Note2</sup>	Avalanche Energy	1764	mJ
$P_D$	Power Dissipation	416.6	W
	Derating Factor above $25^{\circ}\text{C}$	3.33	W/ $^{\circ}\text{C}$
$T_J, T_{stg}$	Operating Junction and Storage Temperature Range	150, $-55$ to $150$	$^{\circ}\text{C}$
$T_L$	Maximum Temperature for Soldering	260	$^{\circ}\text{C}$

Note1: Repetitive Rating: Pulse width limited by maximum junction temperature

Note2:  $L=0.5\text{mH}$ ,  $I_{as}=84\text{A}$ , Start  $T_J=25^{\circ}\text{C}$

## 3. Thermal characteristics

Symbol	Parameter	Max	Units
$R_{\theta JC}$	thermal resistance, Junction-Case	0.3	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	thermal resistance, Junction-Ambient	62.5	$^{\circ}\text{C}/\text{W}$

## 4. Electrical Characteristics

at  $T_C=25^{\circ}\text{C}$ , unless otherwise specified

OFF Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$ , $I_D=250\mu\text{A}$	85	95	--	V
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=85\text{V}$ , $V_{GS}=0\text{V}$	--	--	1	$\mu\text{A}$
		$V_{DS}=68\text{V}$ , $V_{GS}=0\text{V}$ @ $T_C=125^{\circ}\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSS(F)}$	Gate-Source Forward Leakage	$V_{GS}=+20\text{V}$	--	--	100	nA
$I_{GSS(R)}$	Gate-Source Reverse Leakage	$V_{GS}=-20\text{V}$	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Values			Unit
			Min	Typ	Max	
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=50A$	--	1.4	2	m $\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
$C_{iss}$	Input Capacitance	$V_{DS}=42.5V, V_{GS}=0, f=1MHz$	--	14490	--	pF
$C_{oss}$	Output Capacitance		--	2350	--	
$C_{rss}$	Reverse Transfer Capacitance		--	472	--	
$Q_g$	Total Gate Charge	$V_{DD}=42.5V, I_D=50A, V_{GS}=10V$	--	240	--	nC
$Q_{gs}$	Gate-Source charge		--	56	--	
$Q_{gd}$	Gate-Drain charge		--	60	--	
$R_G$	Gate resistance	$V_{GS}=0, V_{DS}=0$		1.5		$\Omega$

Switching Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=42.5V, I_D=10A, V_{GS}=10V, R_G=3\Omega, \text{Resistive Load}$	--	39	--	ns
$t_r$	Rise Time		--	122	--	
$t_{d(off)}$	Turn-Off Delay Time		--	115	--	
$t_f$	Fall Time		--	137	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Values			Units
			Min	Typ	Max	
$I_S$	Continuous Source Current		--	--	300	A
$I_{SM}$	Maximum Pulsed Current		--	--	1200	A
$V_{SD}$	Diode Forward Voltage	$V_{GS}=0V, I_S=50A$	--	--	1.2	V
$T_{rr}$	Reverse Recovery Time	$I_S=30A, V_{GS}=0, di/dt=100A/us$	--	120	--	ns
$Q_{rr}$	Reverse Recovery Charge		--	360	--	nC



## 5. Characteristics Curves

Figure 1. Safe Operating Area

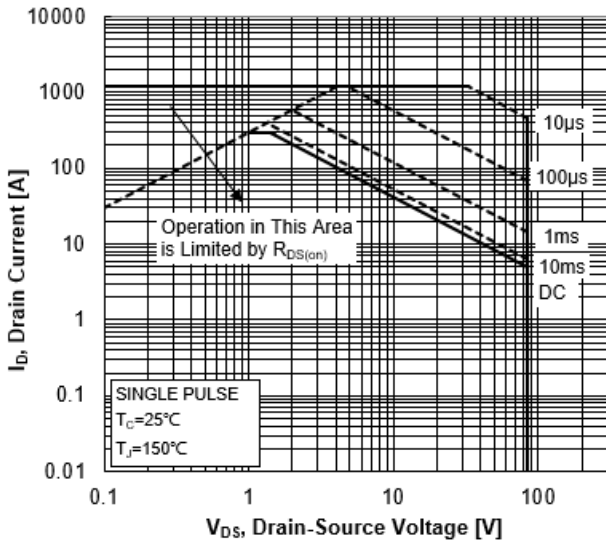


Figure 2. Maximum Power Dissipation vs Case Temperature

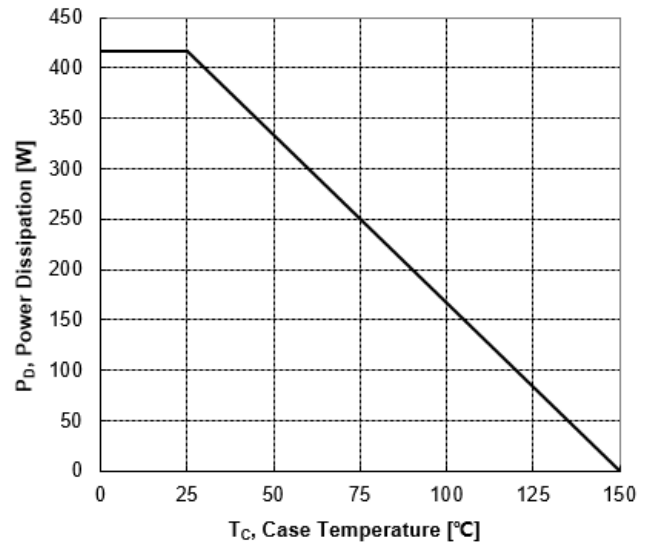


Figure 3. Maximum Continuous Drain Current vs Case Temperature

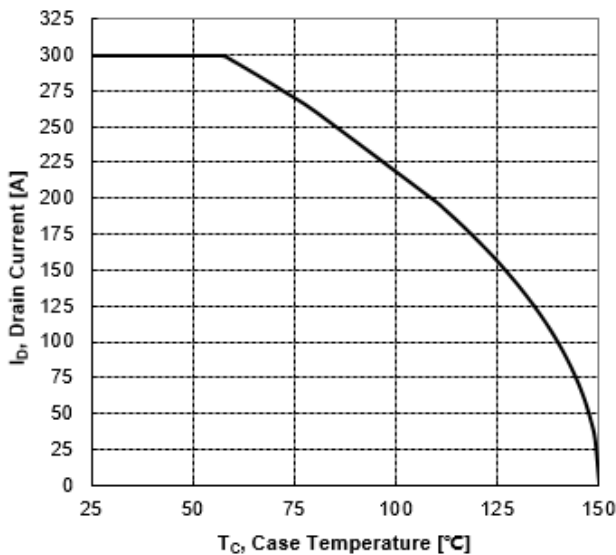


Figure 4. Typical Output Characteristics

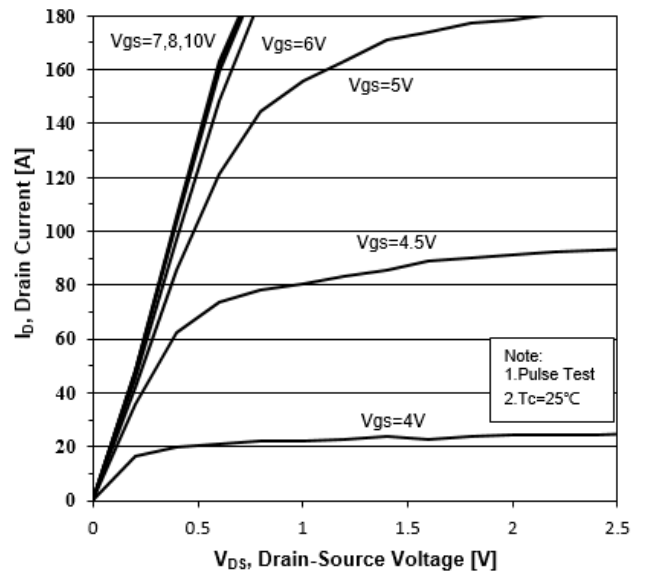




Figure 5. Transient Thermal Impedance

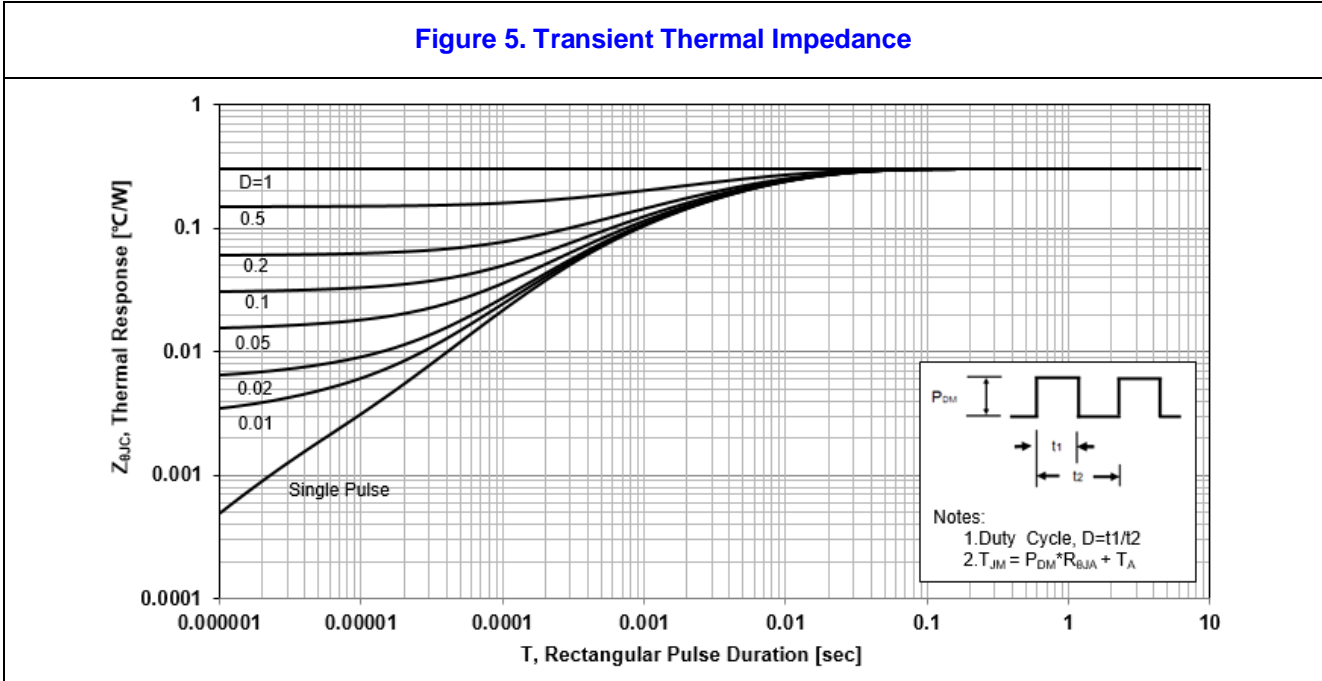


Figure 6. Typical Transfer Characteristics

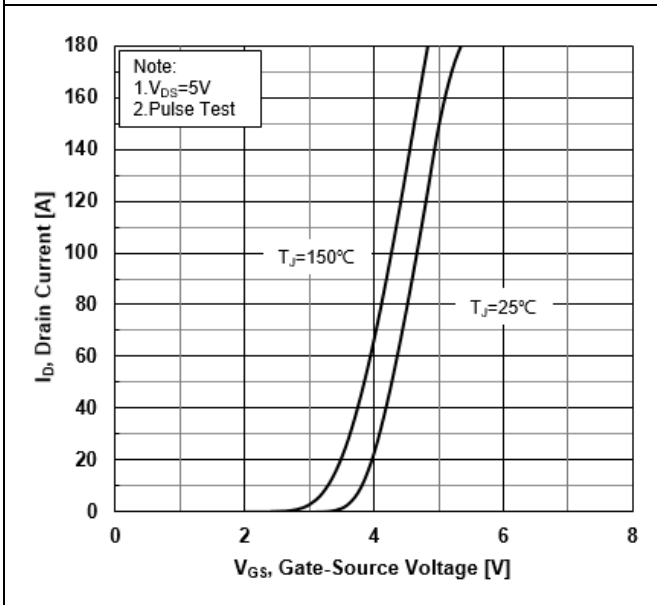
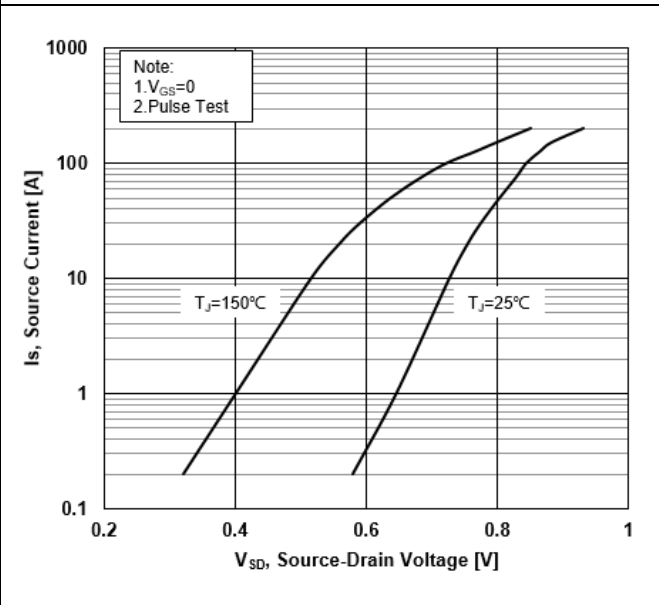
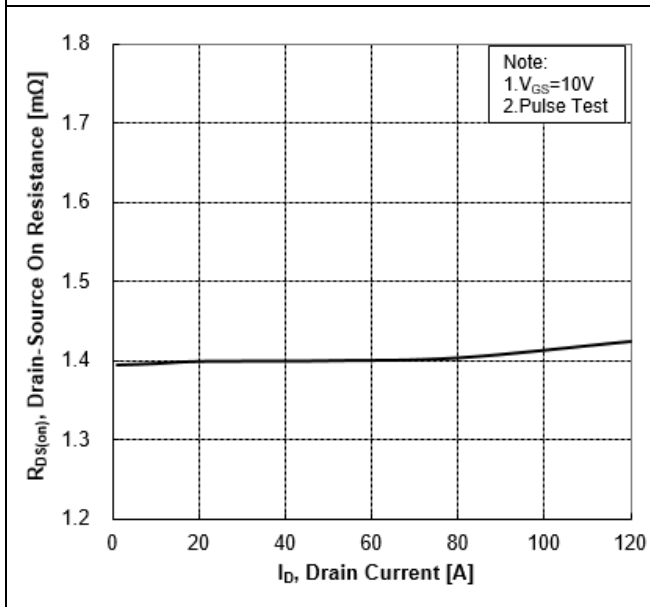


Figure 7. Source-Drain Diode Forward Characteristics

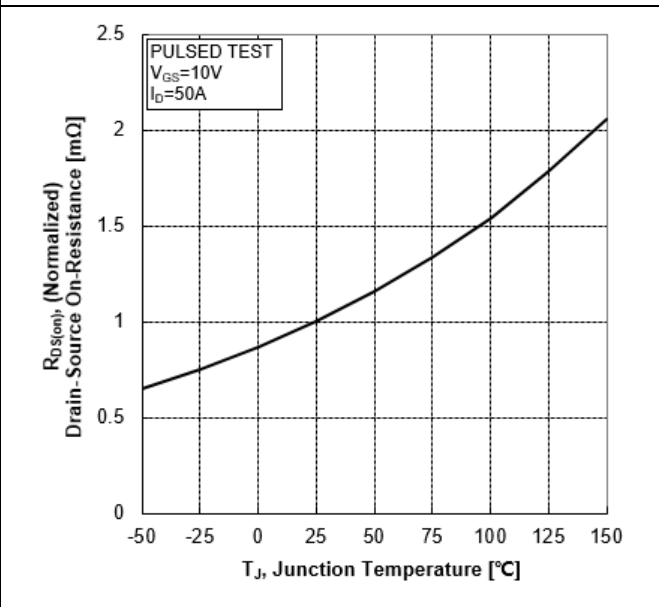




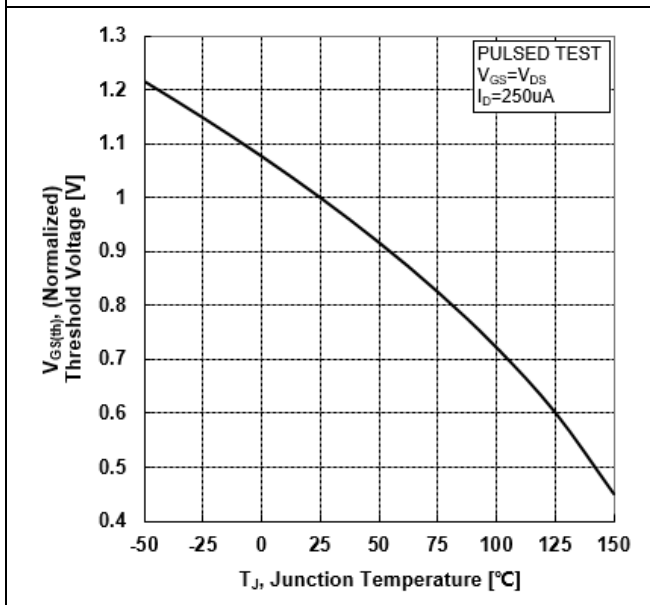
**Figure 8. Drain-Source On-Resistance vs Drain Current**



**Figure 9. Normalized On-Resistance vs Junction Temperature**



**Figure 10. Normalized Threshold Voltage vs Junction Temperature**



**Figure 11. Normalized Breakdown Voltage vs Junction Temperature**

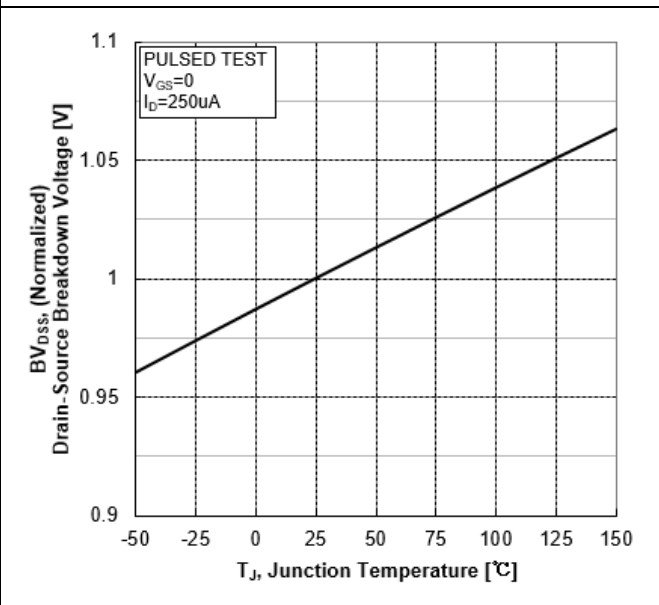




Figure 12. Capacitance Characteristics

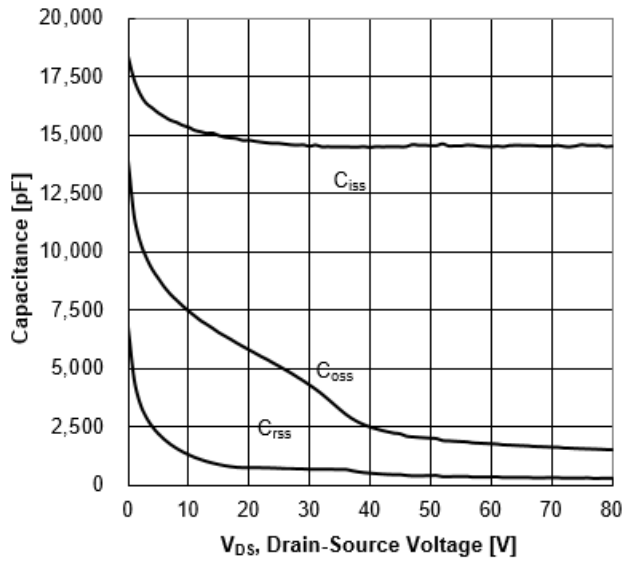
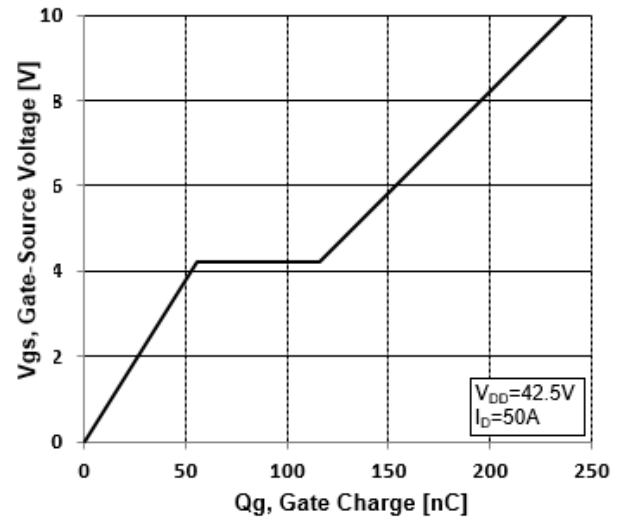


Figure 13. Typical Gate Charge vs Gate-Source Voltage



## 6. Test Circuit and Waveform

Figure 14. Resistive Switching Test Circuit

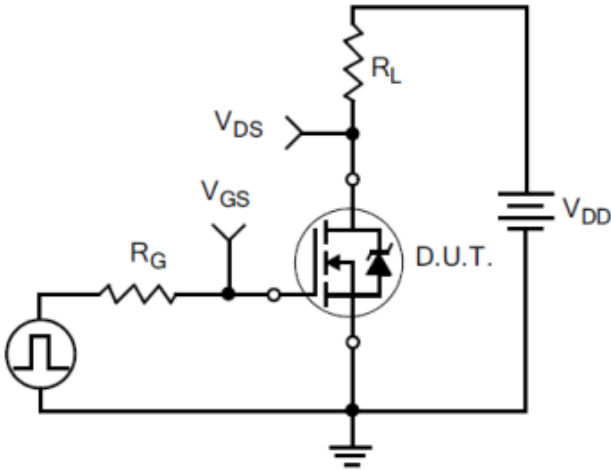


Figure 15. Resistive Switching Waveforms



Figure 16. Gate Charge Test Circuit

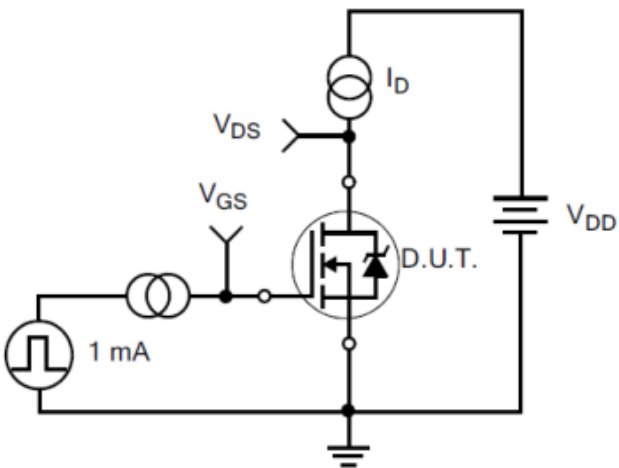


Figure 17. Gate Charge Waveforms

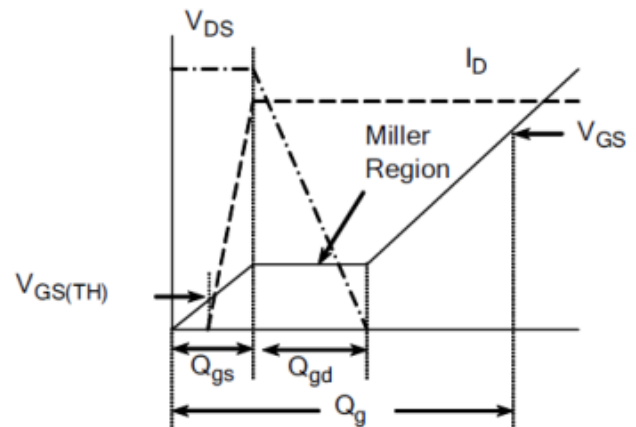






Figure 18. Diode Reverse Recovery Test Circuit

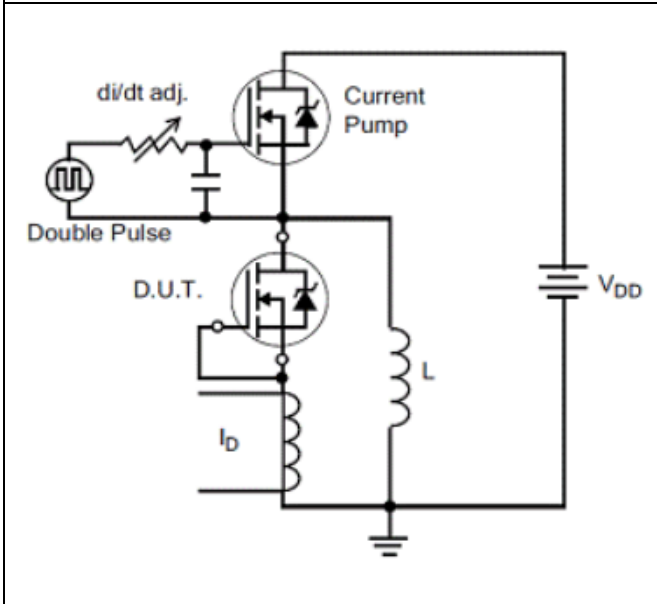


Figure 19. Diode Reverse Recovery Waveform

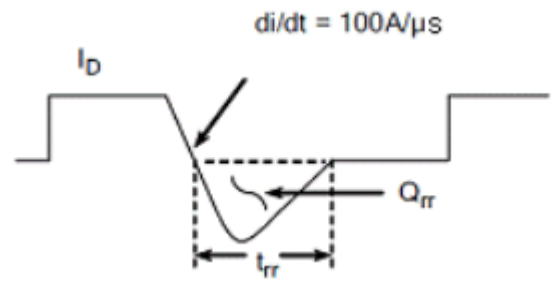


Figure 20. Unclamped Inductive Switching Test Circuit

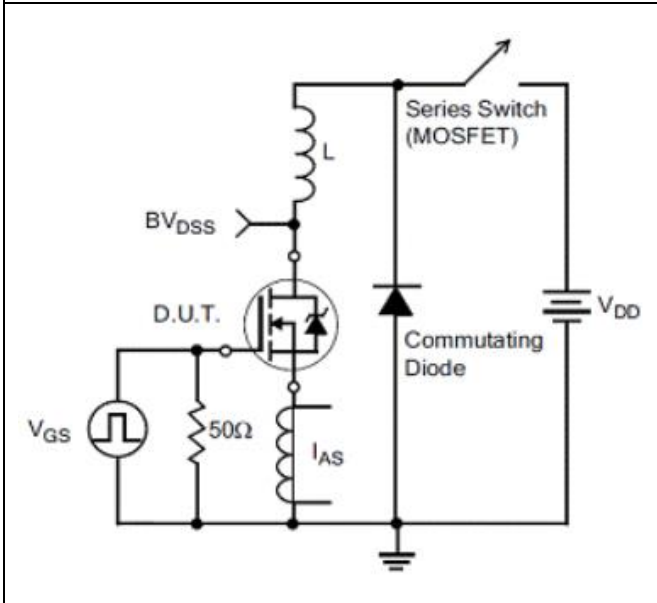
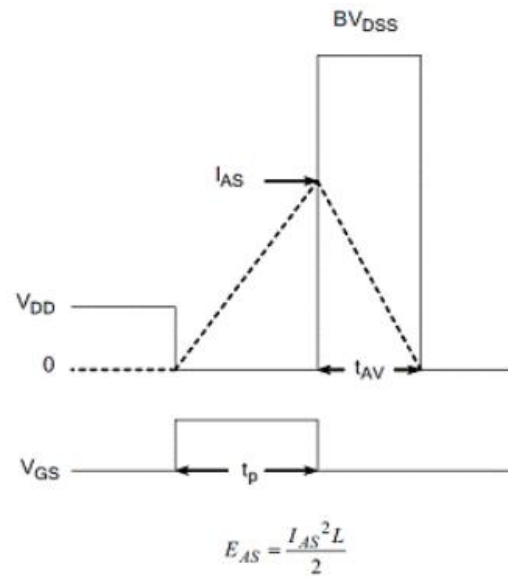
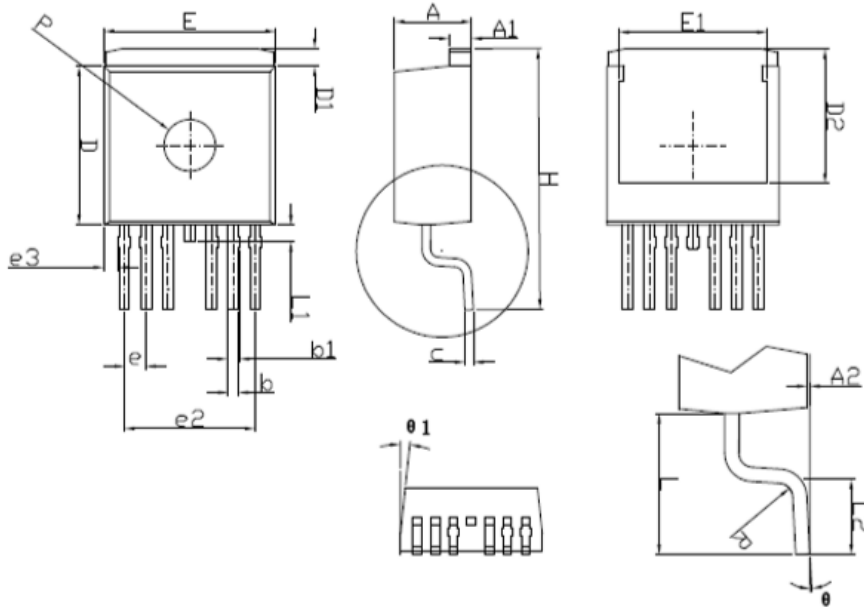


Figure 21. Unclamped Inductive Switching Waveform

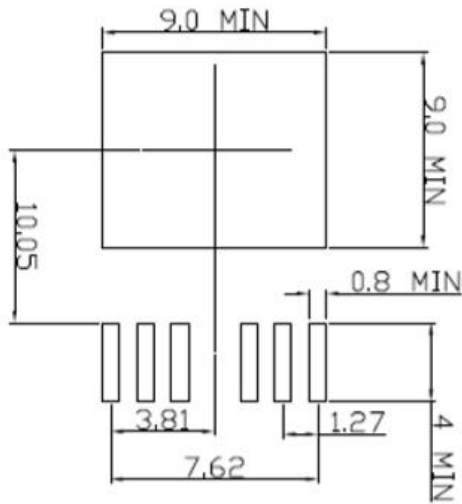




## TO263-7



### RECOMMENDED LAND PATTERN



UNIT: mm

	MIN	NOM	MAX
A	4.30	4.50	4.70
A1	1.20	1.30	1.40
A2	0.05	0.15	0.30
b	0.50	0.60	0.70
b1	0.50	0.70	0.90
c	0.40	0.50	0.60
D	9.05	9.25	9.45
D1	0.70	1.00	1.30
D2	7.35	7.85	8.35
E	9.80	10.00	10.20
E1	8.10	8.60	9.10
e	1.07	1.27	1.47
e2	7.32	7.62	7.92
e3	0.64	0.84	1.04
H	14.65	15.15	15.65
L	4.47	4.97	5.47
L1	0.90	1.20	1.50
L2	2.20	2.50	2.80
θ	0°	3°	8°
θ1	0°	6°	10°
ΦP	2.70	3.00	3.30



**NOTE:**

1. Exceeding the maximum ratings of the device in performance may cause damage to the device, even the permanent failure, which may affect the dependability of the machine. Please do not exceed the absolute maximum ratings of the device when circuit designing.
2. When installing the heat sink, please pay attention to the torsional moment and the smoothness of the heat sink.
3. MOSFETs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.
4. Shanghai Jerrett reserves the right to make changes in this specification sheet and is subject to change without prior notice.